

DERWENT-ACC-NO: 1992-067414

DERWENT-WEEK: 199951

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TITLE: Thin-film FET for memory - has source and
 drain electrodes buried in insulation film between
 upper gate electrode and film covering lower electrode
 NoAbstract Dwg 1/9

PATENT-ASSIGNEE: CASIO COMPUTER CO LTD[CASK]

PRIORITY-DATA: 1990JP-0092021 (April 9, 1990)

PATENT-FAMILY:

PUB-NO	MAIN-IPC	PUB-DATE	LANGUAGE
JP 03290970 A		December 20, 1991	N/A
005	N/A		
JP 2969184 B2		November 2, 1999	N/A
009	H01L 027/115		

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
JP 03290970A	N/A	1990JP-0092021
April 9, 1990		
JP 2969184B2	N/A	1990JP-0092021
April 9, 1990		
JP 2969184B2	Previous Publ.	JP 3290970
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INT-CL (IPC): H01L021/8247, H01L027/11, H01L027/115, H01L029/78
 H01L029/788, H01L029/792

ABSTRACTED-PUB-NO: JP 2969184B

EQUIVALENT-ABSTRACTS:

Optical disk having a resin substrate has a trench on the periphery when the resin substrates are adhered to each other. A groove or pit for tracking is formed on a side of a resin substrate. A 1st ceramics layer, a

recording
layer, 2nd ceramics layer and a reflection layer are laminated in
order. The
plates are adhered using epoxy gp. resin. A trench is formed at the
periphery
and a UV curing type resin is filled into the trench. The resin is
cured and
the periphery is cut.

ADVANTAGE - No change of mechanical characteristics at higher temp..

TITLE-TERMS: THIN FILM FET MEMORY SOURCE DRAIN ELECTRODE BURY
INSULATE FILM

UPPER GATE ELECTRODE FILM COVER LOWER ELECTRODE
NOABSTRACT

DERWENT-CLASS: U11 U12 U13 U14

EPI-CODES: U11-C18B5; U12-B03A; U12-D02A1; U12-Q; U13-C04B2; U14-
A03B7;
U14-H01A,

SECONDARY-ACC-NO:

Non-CPI Secondary Accession Numbers: N1992-050492